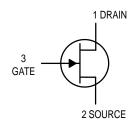
# **JFETs Switching**

# N-Channel — Depletion



# MPF4392 MPF4393

**Motorola Preferred Devices** 

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	Vdc
Drain-Gate Voltage	V <sub>DG</sub>	30	Vdc
Gate–Source Voltage	V <sub>GS</sub>	30	Vdc
Forward Gate Current	I <sub>G(f)</sub>	50	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C
Operating and Storage Channel Temperature Range	T <sub>channel</sub> , T <sub>stg</sub>	-65 to +150	°C



## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I <sub>G</sub> = 1.0 μAdc, V <sub>DS</sub> = 0)		V <sub>(BR)</sub> GSS	30	_	_	Vdc
Gate Reverse Current (V <sub>G</sub> S = 15 Vdc, V <sub>D</sub> S = 0) (V <sub>G</sub> S = 15 Vdc, V <sub>D</sub> S = 0, T <sub>A</sub> = 100°C)		I <sub>GSS</sub>	_		1.0 0.2	nAdc μAdc
Drain–Cutoff Current ( $V_{DS} = 15 \text{ Vdc}$ , $V_{GS} = 12 \text{ Vdc}$ ) ( $V_{DS} = 15 \text{ Vdc}$ , $V_{GS} = 12 \text{ Vdc}$ , $T_{A} = 100^{\circ}\text{C}$ )		I <sub>D(off)</sub>	_	_	1.0 0.1	nAdc μAdc
Gate Source Voltage (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 10 nAdc)	MPF4392 MPF4393	VGS	-2.0 -0.5	_ _	-5.0 -3.0	Vdc
ON CHARACTERISTICS						_
Zero-Gate-Voltage Drain Current(1) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0)	MPF4392 MPF4393	IDSS	25 5.0	_	75 30	mAdc
Drain-Source On-Voltage (I <sub>D</sub> = 6.0 mAdc, V <sub>GS</sub> = 0) (I <sub>D</sub> = 3.0 mAdc, V <sub>GS</sub> = 0)	MPF4392 MPF4393	VDS(on)		_ _	0.4 0.4	Vdc
Static Drain–Source On Resistance ( $I_D = 1.0 \text{ mAdc}, V_{GS} = 0$ )	MPF4392 MPF4393	rDS(on)	_ _		60 100	Ω
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 25 mAdc, f = 1.0 kHz) (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 5.0 mAdc, f = 1.0 kHz)	MPF4392 MPF4393	lуfsl	_	17 12	_ _	mmhos

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 3.0\%$ .

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1



### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Tun	Max	Unit
Cnaracteristic		Syllibol	IVIIII	Тур	IVIAX	Offic
SMALL-SIGNAL CHARACTERISTICS (continued)						
Drain–Source "ON" Resistance $(V_{GS} = 0, I_{D} = 0, f = 1.0 \text{ kHz})$	MPF4392 MPF4393	<sup>r</sup> ds(on)		_ _	60 100	Ω
Input Capacitance ( $V_{GS} = 15 \text{ Vdc}$ , $V_{DS} = 0$ , $f = 1.0 \text{ MHz}$ )		C <sub>iss</sub>	_	6.0	10	pF
Reverse Transfer Capacitance $(V_{GS} = 12 \text{ Vdc}, V_{DS} = 0, f = 1.0 \text{ MHz})$ $(V_{DS} = 15 \text{ Vdc}, I_{D} = 10 \text{ mAdc}, f = 1.0 \text{ MHz})$		C <sub>rss</sub>	_ _ _	2.5 3.2	3.5 —	pF
SWITCHING CHARACTERISTICS		•				
Rise Time (See Figure 2) (I <sub>D(on)</sub> = 6.0 mAdc) (I <sub>D(on)</sub> = 3.0 mAdc)	MPF4392 MPF4393	t <sub>r</sub>	_ _	2.0 2.5	5.0 5.0	ns
Fall Time (See Figure 4) (VGS(off) = 7.0 Vdc) (VGS(off) = 5.0 Vdc)	MPF4392 MPF4393	tf		15 29	20 35	ns
Turn-On Time (See Figures 1 and 2) (I <sub>D(on)</sub> = 6.0 mAdc) (I <sub>D(on)</sub> = 3.0 mAdc)	MPF4392 MPF4393	ton	_ _	4.0 6.5	15 15	ns
Turn-Off Time (See Figures 3 and 4) (VGS(off) = 7.0 Vdc) (VGS(off) = 5.0 Vdc)	MPF4392 MPF4393	<sup>t</sup> off	_ _	20 37	35 55	ns

### **TYPICAL SWITCHING CHARACTERISTICS**

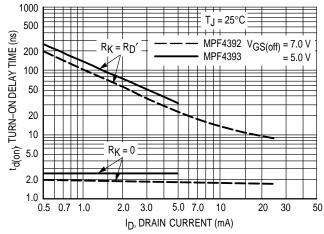


Figure 1. Turn-On Delay Time

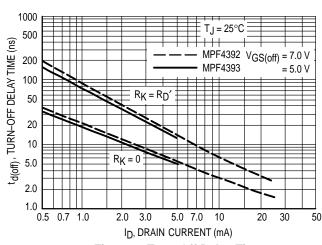


Figure 3. Turn-Off Delay Time

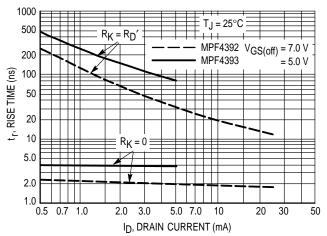


Figure 2. Rise Time

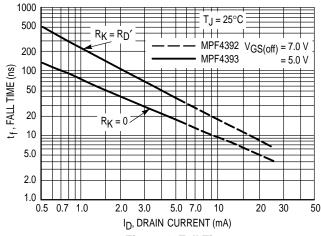


Figure 4. Fall Time

#### $-V_{DD}$ ≶RD SET VDS(off) = 10 V INPUT RT RGEN OUTPUT 50 Ω RGG 50 Ω ≥50Ω $V_{GG}$ $V_{\mathsf{GEN}}$ INPUT PULSE $R_{GG} \gg R_{K}$ $t_{\Gamma} \le 0.25 \text{ ns}$ $R_D' = R_D(R_T + 50)$ $t_f \le 0.5 \text{ ns}$ $R_D + R_T + 50$ PULSE WIDTH = $2.0 \, \mu s$ DUTY CYCLE ≤ 2.0%

Figure 5. Switching Time Test Circuit

#### NOTE 1

The switching characteristics shown above were measured using a test circuit similar to Figure 5. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage (–VGG). The Drain–Source Voltage (VDS) is slightly lower than Drain Supply Voltage (VDD) due to the voltage divider. Thus Reverse Transfer Capacitance (C $_{\rm TSS}$ ) or Gate–Drain Capacitance (C $_{\rm Gd}$ ) is charged to VGG + VDS.

During the turn–on interval, Gate–Source Capacitance ( $C_{gs}$ ) discharges through the series combination of  $R_{Gen}$  and  $R_K$ .  $C_{gd}$  must discharge to  $V_{DS(on)}$  through  $R_G$  and  $R_K$  in series with the parallel combination of effective load impedance ( $R'_D$ ) and Drain–Source Resistance ( $r_{ds}$ ). During the turn–off, this charge flow is reversed.

Predicting turn—on time is somewhat difficult as the channel resistance  $r_{dS}$  is a function of the gate—source voltage. While  $C_{gS}$  discharges,  $V_{GS}$  approaches zero and  $r_{dS}$  decreases. Since  $C_{gd}$  discharges through  $r_{dS}$ , turn—on time is non—linear. During turn—off, the situation is reversed with  $r_{dS}$  increasing as  $C_{gd}$  charges.

The above switching curves show two impedance conditions: 1)  $R_K$  is equal to  $R_D$ ′ which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2)  $R_K = 0$  (low impedance) the driving source impedance is that of the generator.

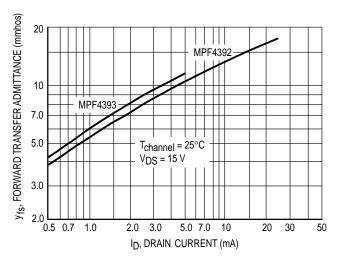


Figure 6. Typical Forward Transfer Admittance

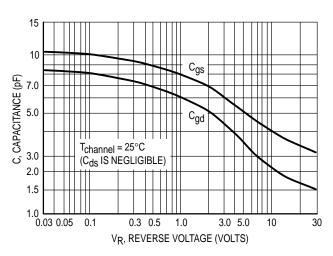


Figure 7. Typical Capacitance

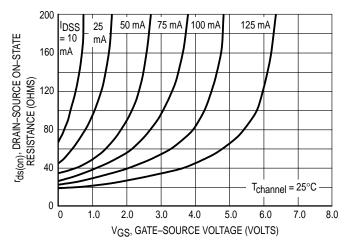


Figure 8. Effect of Gate-Source Voltage On Drain-Source Resistance

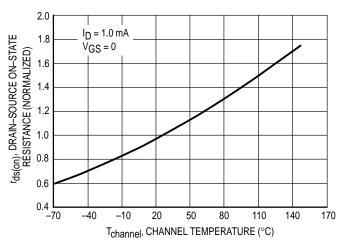


Figure 9. Effect of Temperature On Drain-Source On-State Resistance

#### MPF4392 MPF4393

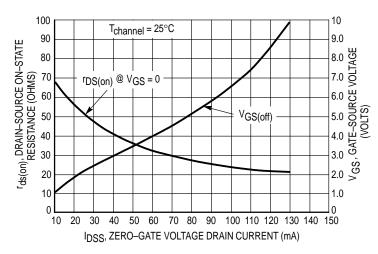


Figure 10. Effect of I<sub>DSS</sub> On Drain-Source Resistance and Gate-Source Voltage

#### NOTE 2

The Zero–Gate–Voltage Drain Current (IDSS), is the principle determinant of other J–FET characteristics. Figure 10 shows the relationship of Gate–Source Off Voltage (VGS(off)) and Drain–Source On Resistance (rds(on)) to IDSS. Most of the devices will be within  $\pm 10\%$  of the values shown in Figure 10. This data will be useful in predicting the characteristic variations for a given part number.

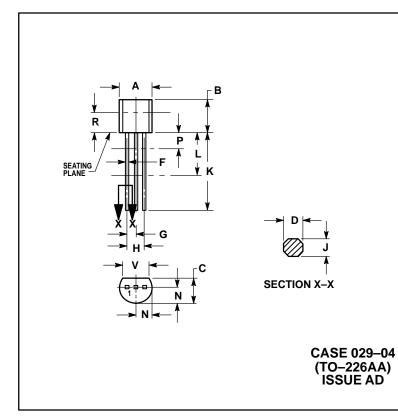
For example:

Unknown

rds(on) and VGS range for an MPF4392

The electrical characteristics table indicates that an MPF4392 has an IDSS range of 25 to 75 mA. Figure 10 shows  $r_{dS(ON)}$  = 52 Ohms for IDSS = 25 mA and 30 Ohms for IDSS = 75 mA. The corresponding VGS values are 2.2 volts and 4.8 volts.

### **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. DIMENSION FAPPLIES BETWEEN P AND L. DIMENSION D AND J. APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

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